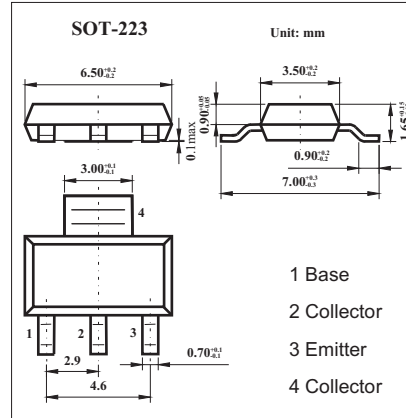


**FZT1151A**

■ Features

- Low saturation Voltage
- High Gain



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-45	V
Collector-emitter voltage	$V_{CE0}$	-40	V
Emitter-base voltage	$V_{EB0}$	-5	V
Continuous Collector Current	$I_C$	-3	A
power dissipation	$P_C$	2.5	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{CB0}$	$I_C = -100 \mu\text{A}$	-45			V
Collector to emitter breakdown voltage	$V_{CE0}$	$I_C = -10\text{mA}$	-40			V
Emitter to base breakdown voltage	$V_{EB0}$	$I_E = -100 \mu\text{A}$	-5.0			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -36\text{V}, I_E = 0$			-100	nA
Emitter Cut-Off Current	$I_{EBO}$	$V_{EB} = -4\text{V}, I_C = 0$			-100	nA
DC current gain	$h_{FE}$	$I_C = -10\text{mA}; V_{CE} = -2\text{V}$	270	450		
		$I_C = -500\text{mA}; V_{CE} = -2\text{V}$	250		800	
		$I_C = -2\text{A}; V_{CE} = -2\text{V}$	180	300		
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1.8\text{A}; I_B = -70\text{mA}$			-0.26	V
		$I_C = -3\text{A}; I_B = -250\text{mA}$			-0.3	V
Output capacitance	$C_{ob}$	$V_{CB} = -10\text{V}, I_E = 0, f = 1.0\text{MHz}$		40		pF
Transition frequency	$f_T$	$I_C = -50\text{mA}; V_{CE} = -10\text{V}; f = 50\text{MHz}$		145		MHz

■ Marking

Marking	1151A
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